



20V 175°C P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C
201	$38m\Omega$ @ $V_{GS} = -4.5V$	-5.6A
-20V	52mΩ @ V _{GS} = -2.5V	-4.8A

Features and Benefits

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- Low Input Capacitance
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

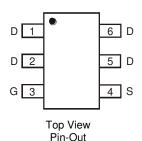
- DC-DC Converters
- Motor Control
- Power Management Functions
- Analog Switch

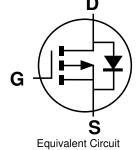
Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.013 grams (Approximate)









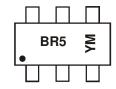
Ordering Information (Note 5)

Part Number	Case	Packaging
DMPH2040UVTQ-7	TSOT26	3,000/Tape & Reel
DMPH2040UVTQ-13	TSOT26	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, see https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



BR5 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	20	021	2022	2023	3	2	2024	2025	20:	26	2027
Code	G	Н		1	J	K			L	М	N	l	0
Month	Jan	Feb	Mar	Apr	May	Jun	Jı	ul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	7	8	9	0	N	D



Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	-20	V		
Gate-Source Voltage	V_{GSS}	±12	V		
Continuous Drain Current (Note 7) V _{GS} = -4.5V	Ι _D	-5.6 -3.9	Α		
Continuous Drain Current (Note 8) V _{GS} = -4.5V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	l _D	-11.7 -8.3	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-40	Α		
Continuous Source-Drain Diode Current (Note 7)	Is	-2.0	A		

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

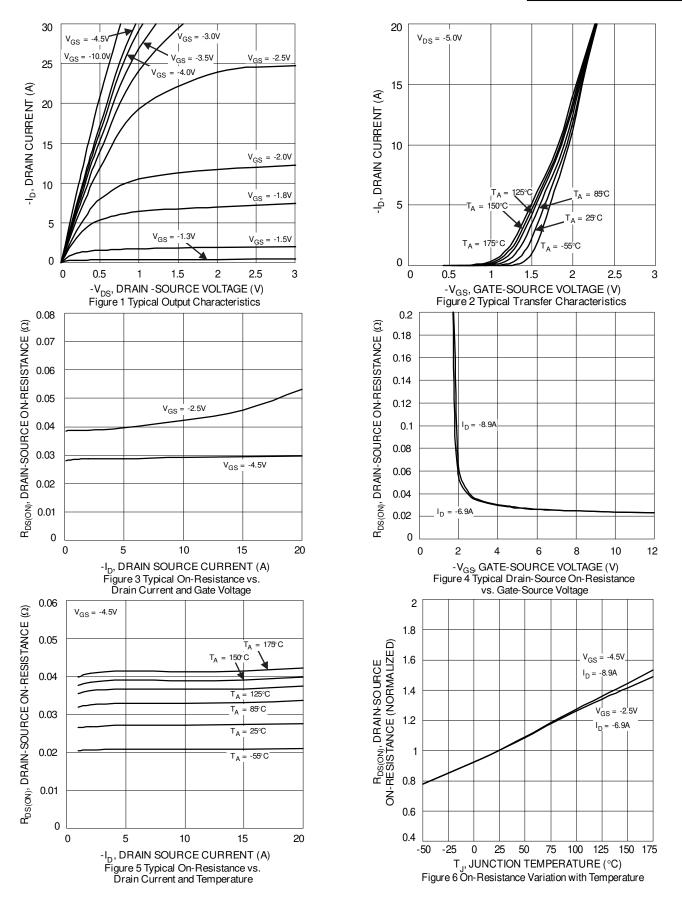
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{OJA}	125	°C/W
Total Power Dissipation (Note 7)	T _A = +25°C	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R _{OJA}	83	°C/W
Thermal Resistance, Junction to Case (Note 8)	Steady State	Rejc	19	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +175	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

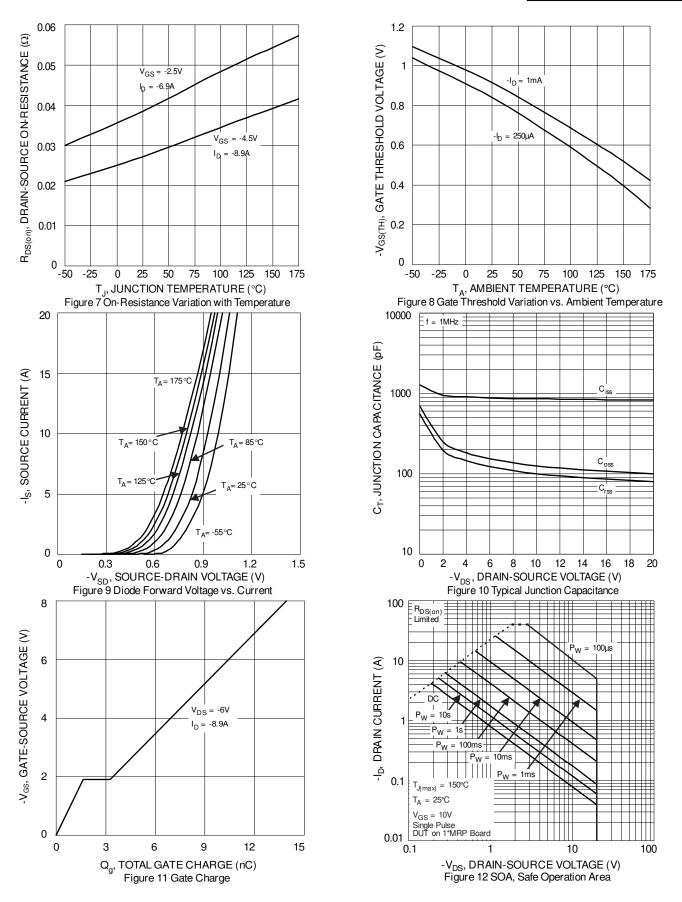
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)				1		1
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)				<u> </u>		
Gate Threshold Voltage	$V_{GS(TH)}$	-0.6	_	-1.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	_	_	27	38	mΩ	$V_{GS} = -4.5V, I_D = -8.9A$
Static Drain-Source On-nesistance	R _{DS(ON)}	_	38	52	11122	$V_{GS} = -2.5V, I_D = -6.9A$
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	V _{GS} = 0V, I _S = -2.9A
DYNAMIC CHARACTERISTICS (Note 10)				•		•
Input Capacitance	C _{iss}	_	834	_		10///
Output Capacitance	Coss	_	133	_	pF	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	105	_		
Gate Resistance	R _G	_	4.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	8.6	_		
Total Gate Charge (V _{GS} = -8V)	Qg	_	19	_	nC	V 0V 1 0 0 0
Gate-Source Charge	Qgs	_	1.5	_	li li C	$V_{DS} = -6V, I_{D} = -8.9A$
Gate-Drain Charge	Q_{gd}	_	2.5	_		
Turn-On Delay Time	t _{D(ON)}	_	5.8	_		
Turn-On Rise Time	t _R	_	7.7	_]	$V_{DD} = -6V, R_L = 6\Omega$
Turn-Off Delay Time	t _{D(OFF)}	_	28.1	<u> </u>	ns	$V_{GS} = -4.5V, R_G = 6\Omega, I_D = -1A$
Turn-Off Fall Time	t _F	_	14.6	_		
Body Diode Reverse Recovery Time	t _{RR}	_	9.8	_	ns	$I_F = -8.9A$, $di/dt = -100A/\mu s$
Body Diode Reverse Recovery Charge	Q _{RR}	_	2.7	_	nC	$I_F = -8.9A$, $di/dt = -100A/\mu s$

- 6. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
 7. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 8. Thermal resistance from junction to soldering point (on the exposed drain pad).
 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.











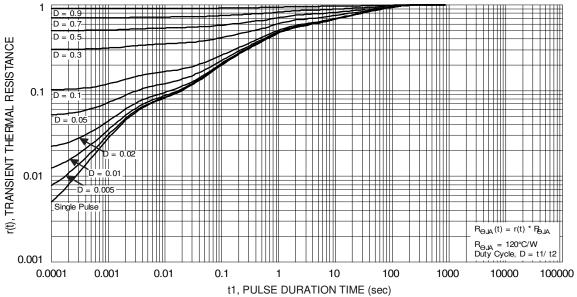
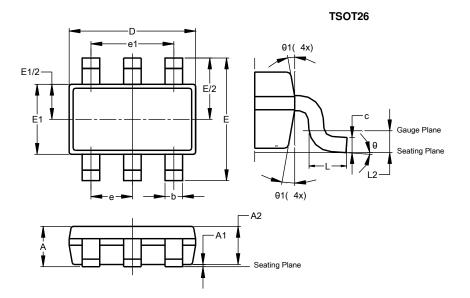


Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

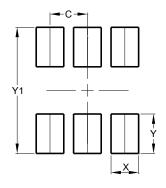


TSOT26							
Dim	Min	Max	Тур				
Α	_	1.00	_				
A1	0.010	0.100	_				
A2	0.840	0.900	_				
D	2.800	3.000	2.900				
Е	2	.800 BS	C				
E1	1.500	1.700	1.600				
۵	0.300	0.450	_				
C	0.120	0.200	_				
e	0.950 BSC						
e1	1	.900 BS	iC				
L	0.30 0.50 —		_				
L2	0	.250 BS					
θ	0°	8°	4°				
θ1	4°	12°	_				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Υ	1.000
Y1	3.199



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